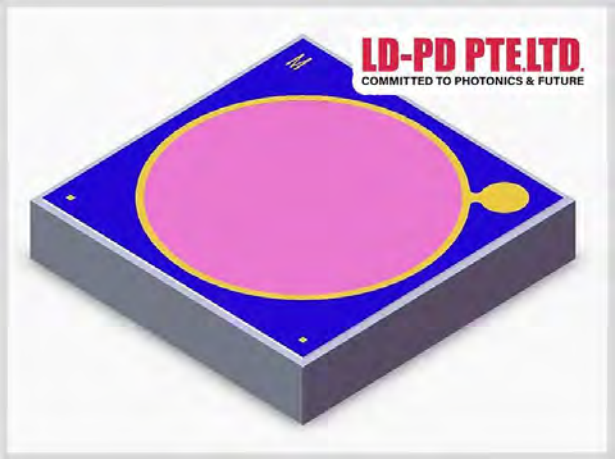
2600nm Extended InGaAs/InP PIN PD Chip



Description

Extended InGaAs Photodiodes Chips, high sensitivity photo-diode for use in infrared instrumentation and sensing applications. High spectral response in the region 900 nm to 2600 nm.

Features

- High responsivity
- Cutoff wavelength: 2.5-2.6um
- Low dark current
- Top illuminated planar structure

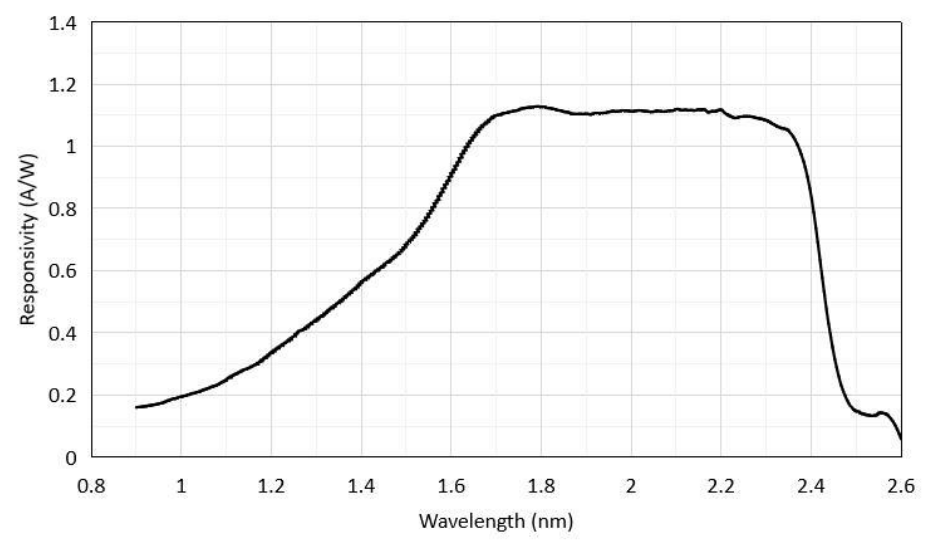
Specifications

PARAMETER	SYMBOL	ACTIVE AREA (um)	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Response range	λ	All	1000		2600	nm	
Responsivity	R	All		1.0		A/W	λ=2300nm
Capacitance	C	Φ300		120		pF	VR=-1V, f= 1MHz
		Φ500		160			
		Φ1000		300			

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Dark current	ID	Φ300		1.0	2.0	uA	VR=-0.5V
		Φ500		3.0	6.0		
		Φ1000		5.0	10.0		
Breakdown	Vbr	All	2				I= 10uA

Spectral Response



Absolute Maximum Ratings

PARAMETER	SYMBOL	VALUE	UNIT
Reverse voltage	VRmax	1	V
Forward Current		10	mA
Operating temperature	Topr	−40 to +85	℃
Storage temperature	Tstg	−40 to +100	℃

Dimension Parameter

PARAMETER	SYMBOL	Φ300	Φ500	Φ1000	UNIT
Active area diameter	-	300	500	1000	μm
Bond pad diameter	-	80	80	120	μm
Die size	-	420x420	600x600	1250x1250	μm
Die thickness	t	180±20	180±20	180±20	μm

Precautions for use

This chip is susceptible to damage as a result of ESD. Use of ground straps, antistatic mats, and other standard ESD protective equipment is requisite when handling or testing an InGaAs or GaAs PIN/APD chip.

Application

- Gas analyzers
- Moisture meters
- Near-infrared sensing
- Optical power meters

Ordering Info

PN#LD-PD300L-2600
Response Range: 900-2600nm, Active area diameter:300um, Bare Chip
PN#LD-PD500L-2600
Response Range: 900-2600nm, Active area diameter:500um, Bare Chip
PN#LD-PD1000L-2600
Response Range: 900-2600nm, Active area diameter:1000um, Bare Chip